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(54) **OPTICAL DISK PROTECTIVE FILM AND SPUTTERING TARGET FOR FORMATION OF THAT PROTECTIVE FILM**

(57) Abstract:

PROBLEM TO BE SOLVED: To permit DC sputtering, to decrease the production of particles to increase the production efficiency, and to provide a protective film having large transmittance and low reflectance by using a sputtering target essentially comprising ZnO and if necessary by adding other oxides.

SOLUTION: The sputtering target for the formation of an protective film of an optical disk is produced by sintering one or more oxides of ZnO, In2O3 and SnO2 as the main component with addition of Al2O3 or Ga2O3 if necessary by 0.1 to 20 wt.%. The content of Al2O3 and Ga2O3 is preferably controlled to 0.1 to 20 wt.%, and thereby, the bulk electric resistance of the target can be controlled and the transmittance in the visible ray region of the protective film after the protective film is formed can be maintained to ≧80%. Further, ZrO2 and/or TiO2 are incorporated by 0.01 to 5 wt.%.